

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
1	BRS	L3	3	dop\$3 with (semiconductor or silicon) same (polysilicon or polycrystall\$5 or armophous) and (ion or RTA or anneal\$3) and bur\$5 near oxide with epitaxial\$2 with (heat\$4 or thermal\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 12:42			
2	BRS	L4	4	dop\$3 with (semiconductor or silicon) and (polysilicon or polycrystall\$5 or armophous) and (ion or RTA or anneal\$3) and bur\$5 near oxide with epitaxial\$2 with (heat\$4 or thermal\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 12:43			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
3	BRS	L8	0	(438/542).ccls. and (\$3MOS near transistor or mosfet) and dop\$3 with (semiconductor or silicon) same (polysilicon or polycrystall\$5 or amorphous) and (ion or RTA or anneal\$3) and oxide with epitaxial\$2 with (heat\$4 or thermal\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 13:38			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Co mm en ts	Er ro r De fi ni ti on	Er ro rs
4	BRS	L9	1	(438/308).ccls. and (\$3MOS near transistor or mosfet) and dop\$3 with (semiconductor or silicon) same (polysilicon or polycrystall\$5 or amorphous) and (ion or RTA or anneal\$3) and oxide with epitaxial\$2 with (heat\$4 or thermal\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 12:52			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
5	BRS	L10	7	(438/309).cccls. and (\$3MOS near transistor or mosfet) and dop\$3 with (semiconductor or silicon) same (polysilicon or polycrystal\$5 or amorphous) and (ion or RTA or anneal\$3) and oxide with epitaxial\$2 with (heat\$4 or thermal\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 12:56			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
6	BRS	L11	76	("438"/\$).ccls. and (MOS near transistor or mosfet) and dop\$3 with (semiconductor or silicon or substrate) with surface same (polysilicon or polycrystal\$5 or amorphous) and (ion or RTA or anneal\$3) and oxide with epitaxial\$2 with (heat\$4 or thermal\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 12:57			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Co mm en ts	Er ro r De fi ni ti on	Er ro rs
7	BRS	L12	91	("438"/\$).ccls. and (MOS or mosfet) and dop\$3 with (semiconductor or silicon or substrate) with surface same (polysilicon or polycrystal\$5 or amorphous) and (ion or RTA or anneal\$3) and oxide with epitaxial\$2 with (heat\$4 or thermal\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 13:00			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
8	BRS	L13	72	("438"/\$).ccls. and (MOS or mosfet) and dop\$3 with (semiconductor or silicon or substrate) with surface same (polysilicon or polycrystal1\$5 or amorphous) and (ion or RTA or anneal\$3) and oxide with epitaxial\$2 with (heat\$4 or thermal\$4) and @AD < "20011207"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 13:07			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Co mm en ts	Er ro r De fi ni ti on	Er ro rs
9	BRS	L14	4	("438"/\$).ccls. and (MOS or mosfet) and dop\$3 with (semiconductor or silicon or substrate) with surface same (polysilicon or polycrystall\$5 or amorphous) and (ion or RTA or anneal\$3) and bur\$4 with dop\$4 with epitaxial\$2 with (heat\$4 or thermal\$4) and @AD < "20011207"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 13:13			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
10	BRS	L15	3	("438"/\$).ccls. and (MOS or mosfet) and dop\$3 with (semiconductor or silicon or substrate) with surface same (polysilicon or polycrystall\$5 or amorphous) and (ion or RTA or anneal\$3) and bur\$4 with dop\$4 with (form\$4 or produc\$4) with epitaxial\$2 with (heat\$4 or thermal\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 13:18			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Com men ts	Er ro r De fi ni ti on	Er ro rs
11	BRS	L16	2	("438"/\$).ccls. and (MOS or mosfet) and dop\$3 with (semiconductor or silicon or substrate) with surface same (polysilicon or polycrystall\$5 or armophous) and (ion or RTA or anneal\$3) and bur\$4 with dop\$4 with (form\$4 or produc\$4) with epitaxial\$2 with (heat\$4 or thermal\$4) and @AD<"20010712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 13:18			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Com men ts	Er ro r De fi ni ti on	Er ro rs
12	BRS	L17	3	("438"/\$).cccls. and (MOS or mosfet) and dop\$3 with (semiconductor or silicon or substrate) with surface same (polysilicon or polycrystall\$5 or armophous) and (ion or RTA or anneal\$3) and bur\$4 with dop\$4 with (form\$4 or produc\$4) with epitaxial\$2 with (heat\$4 or thermal\$4) and @AD < "20011207"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 13:23			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Com men ts	Er ro r De fi ni ti on	Er ro rs
13	BRS	L18	4	(MOS or mosfet) and dop\$3 with (semiconductor or silicon or substrate) with surface same (polysilicon or polycrystall\$5 or amorphous) and (ion or RTA or anneal\$3) and bur\$4 with dop\$4 with (form\$4 or produc\$4) with epitaxial\$2 with (heat\$4 or thermal\$4) and @AD < "20011207"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 13:27			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Co mm en ts	Er ro r De fi ni ti on	Er ro rs
14	BRS	L21	1	(MOS or mosfet) and form\$3 with epitaxial\$2 with (heat\$4 or thermal\$4) and buried near doping and @AD < "20011207"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 13:32			
15	BRS	L22	66	(MOS or mosfet) and form\$3 with epitaxial\$2 with (heat\$4 or thermal\$4) and buried with doping and @AD < "20011207"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 13:32			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Co mm en ts	Er ro r De fi ni ti on	Er ro rs
16	BRS	L23	21	(MOS or mosfet) and form\$3 with epitaxial\$2 with (heat\$4 or thermal\$4) and buried with doping and (polycrystalline or amorphous) and @AD < "20011207"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 13:33			
17	BRS	L28	2	((MOS or mosfet) and epitaxial\$2 with (heat\$4 or thermal\$4) and dop\$3 and (polycrystalline or amorphous)).clm .	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 13:35			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Co mm en ts	Er ro r De fi ni ti on	Er ro rs
18	BRS	L29	1	(438/542).ccls. and (MOS or mosfet) and dop\$3 with (semiconductor or silicon) same (polysilicon or polycrystal1\$5 or amorphous) and (ion or RTA or anneal\$3) and epitaxial\$2 with (heat\$4 or thermal\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 13:39			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Co mm en ts	Er r De fi ni ti on	Er ro rs
19	BRS	L31	4	((MOS or mosfet) and dop\$3 with (semiconductor or silicon or sustrate) same (polysilicon or polycrystall\$5 or armophous) and (ion or RTA or anneal\$3) and epitaxial\$2 with (heat\$4 or thermal\$4)).clm .	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 13:43			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
20	BRS	L33	103	(MOS or mosfet) and dop\$3 with (semiconductor or silicon or substrate) same (polycrystall\$5 or amorphous) and (ion or RTA or anneal\$3) and epitaxial\$2 with (heat\$4 or thermal\$4) and bur\$4 with dop\$4	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 13:45			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Co mm en ts	Er r De fi ni ti on	Er ro rs
21	BRS	L34	85	(MOS or mosfet) and dop\$3 with (semiconductor or silicon or substrate) same (polycrystall\$5 or armophous) and (ion or RTA or anneal\$3) and epitaxial\$2 with (heat\$4 or thermal\$4) and bur\$4 with dop\$4 and @AD < "20010712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 13:45			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
22	BRS	L35	43	("438"/\$).ccls. and (MOS or mosfet) and dop\$3 with (semiconductor or silicon or substrate) same (polycrystalline or amorphous) and (ion or RTA or anneal\$3) and epitaxial\$2 with (heat\$4 or thermal\$4) and bur\$4 with dop\$4 and @AD < "20010712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 14:05			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Co mm en ts	Er ro r De fi ni ti on	Er ro rs
23	BRS	L36	31	("4116720" "4454647" "4473598" "4520552" "4689871" "4745081" "4803535" "4816421" "4829017" "4847214" "4873560" "4910567" "4918502").PN. OR ("5077228").URP N.	US-PGPUB; USPAT; USOCR	2006/02/02 14:03			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
24	BRS	L37	0	(438/514).ccls. and (MOS or mosfet) and dop\$3 with (semiconductor or silicon or substrate) same (polycrystalline or amorphous) and (ion or RTA or anneal\$3) and epitaxial\$2 with (heat\$4 or thermal\$4) and bur\$4 with dop\$4 and @AD < "20010712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 14:05			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
25	BRS	L38	0	(438/482).ccls. and (MOS or mosfet) and dop\$3 with (semiconductor or silicon or substrate) same (polycrystalline or amorphous) and (ion or RTA or anneal\$3) and epitaxial\$2 with (heat\$4 or thermal\$4) and bur\$4 with dop\$4 and @AD < "20010712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 14:05			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Co mm en ts	Er ro r De fi ni ti on	Er ro rs
26	BRS	L39	0	(438/488).ccls. and (MOS or mosfet) and dop\$3 with (semiconductor or silicon or substrate) same (polycrystall\$5 or amorphous) and (ion or RTA or anneal\$3) and epitaxial\$2 with (heat\$4 or thermal\$4) and bur\$4 with dop\$4 and @AD < "20010712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 14:05			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
27	BRS	L40	0	(438/506).ccls. and (MOS or mosfet) and dop\$3 with (semiconductor or silicon or substrate) same (polycrystall\$5 or amorphous) and (ion or RTA or anneal\$3) and epitaxial\$2 with (heat\$4 or thermal\$4) and bur\$4 with dop\$4 and @AD < "20010712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 14:05			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Co mm en ts	Er ro r De fi ni ti on	Er ro rs
28	BRS	L41	0	(438/511).ccls. and (MOS or mosfet) and dop\$3 with (semiconductor or silicon or substrate) same (polycrystall\$5 or amorphous) and (ion or RTA or anneal\$3) and epitaxial\$2 with (heat\$4 or thermal\$4) and bur\$4 with dop\$4 and @AD < "20010712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 14:05			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
29	BRS	L42	0	(438/522).ccls. and (MOS or mosfet) and dop\$3 with (semiconductor or silicon or substrate) same (polycrystall\$5 or amorphous) and (ion or RTA or anneal\$3) and epitaxial\$2 with (heat\$4 or thermal\$4) and bur\$4 with dop\$4 and @AD < "20010712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 14:06			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
30	BRS	L43	0	(438/526).ccls. and (MOS or mosfet) and dop\$3 with (semiconductor or silicon or substrate) same (polycrystalline or amorphous) and (ion or RTA or anneal\$3) and epitaxial\$2 with (heat\$4 or thermal\$4) and bur\$4 with dop\$4 and @AD < "20010712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 14:06			

	Type	L #	Hits	Search Text	DBs	Time Stamp	Comments	Error Definition	Errors
31	BRS	L44	0	(438/530).ccls. and (MOS or mosfet) and dop\$3 with (semiconductor or silicon or substrate) same (polycrystall\$5 or amorphous) and (ion or RTA or anneal\$3) and epitaxial\$2 with (heat\$4 or thermal\$4) and bur\$4 with dop\$4 and @AD < "20010712"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	2006/02/02 14:06			